NEC

PNP SILICON TRANSISTOR 2SA1460

DESCRIPTION

The 2SA1460 is designed for power amplifier and high

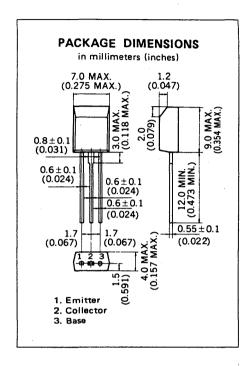
speed switching applications.

FEATURES

- High speed, high voltage switching.
- Low Collector Saturation Voltage.
- Complementary to the NEC 2SC3733 NPN transistor.

ABSOLUTE MAXIMUM RATINGS

* PW \leq 10 ms, Duty Cycle \leq 50 %



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
ton	Turn-on Time		25	40	ns)	Vcc = -10 V
^t stg	Storage Time		46	70	ns }	I _C = -500 mA
toff	Turn-off Time		62	100	ns	$I_{B1} = -I_{B2} = -50 \text{ mA}$
fT	Gain Bandwidth Product	300	400		MHz	$V_{CE} = -10 \text{ V, I}_{E} = 100 \text{ mA}$
Cob	Output Capacitance		. 11	25	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
hFE1*	DC Current Gain	60	120	200	_	$V_{CE} = -10 \text{ V, I}_{C} = -50 \text{ mA}$
hFE2*	DC Current Gain	60	150		_	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$
V _{CE(sat)} *	Collector Saturation Voltage		-0.26	-0.60	V	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$
V _{BE(sat)} *	Base Saturation Voltage		-0.98	-1.20	V	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$
ICES	Collector Cutoff Current	•		-0.5	μΑ	$V_{CB} = -45 \text{ V, R}_{BE} = 0$
I _{EBO}	Emitter Cutoff Current			-0.5	μА	$V_{EB} = -4.0 \text{ V, I}_{C} = 0$

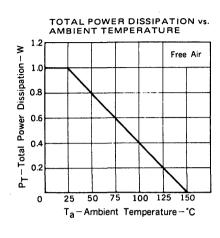
^{*} Pulsed PW \leq 350 μ s, Duty Cycle \leq 2 %

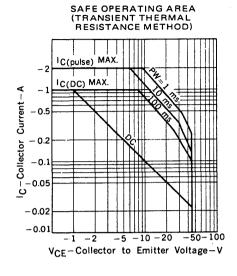
Classification of h_{FE1}

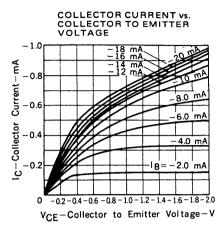
Rank	L	κ
Range	60 to 120	100 to 200

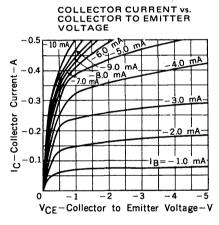
 h_{FE1} Test Conditions: $V_{CE} = -10 \text{ V}$, $I_{C} = -50 \text{ mA}$

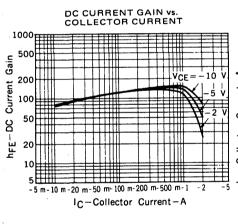
TYPICAL CHARACTERISTICS (Ta = 25 °C)

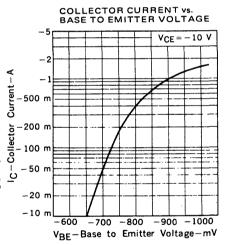


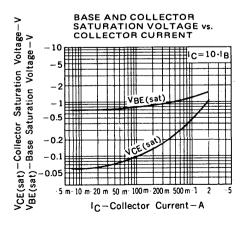


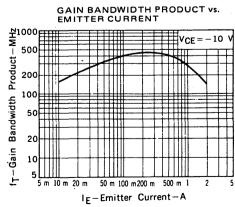


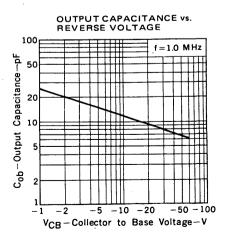


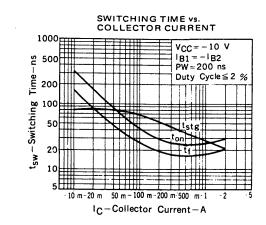












SWITCHING TIME TEST CIRCUIT

